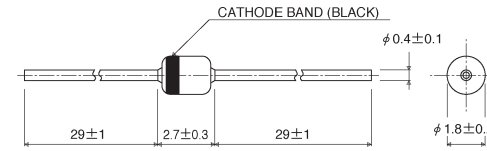
Schottky barrier diode
RB721Q–40

●Applications
High speed switching

●Features
1) Glass–sealed envelope for high reliability. (MSD)
2) Small pitch enables insertion on PCBs.
3) Low reverse current and low forward voltage.

●Construction
Silicon epitaxial

●External dimensions (Units: mm)



ROHM : MSD
JEDEC : DO - 34

Product identification number "S2" is stamped on body of main unit.

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	30	mA
Peak forward surge current*	I_{FSM}	200	mA
Junction temperature	Tj	125	℃
Storage temperature	Tstg	−40～+125	℃

* 60 Hz for 1 ∽

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	0.31	0.37	V	I_F=1mA
Reverse current	I_R	—	0.06	0.5	μA	V_R=25V
Capacitance between terminals	C_T	—	2.0	—	pF	V_R=1V, f=1MHz

* ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

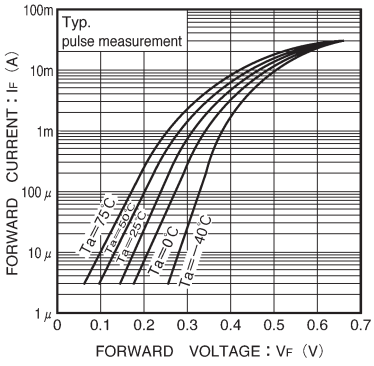


Fig. 1 Forward characteristics

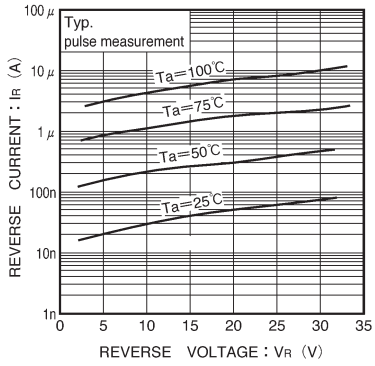


Fig. 2 Reverse characteristics

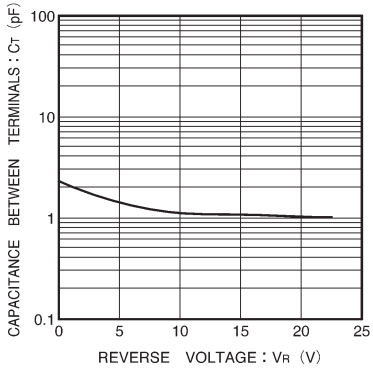


Fig. 3 Capacitance between terminals characteristics

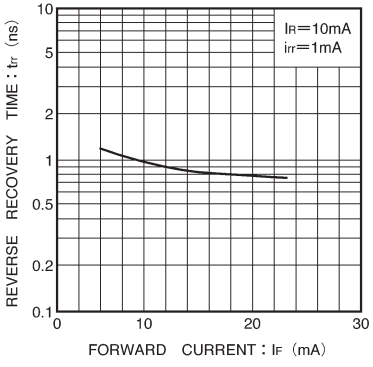


Fig. 4 Reverse recovery time characteristics

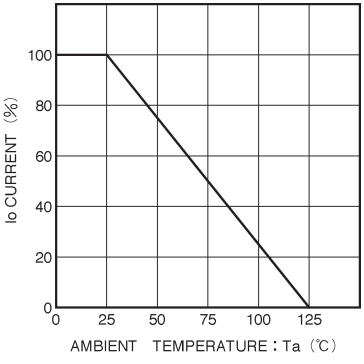


Fig. 5 Derating curve (mounting on glass epoxy PCBs)